

Application No.: filed concurrently  
Preliminary Amendment  
July 8, 2003

IN THE CLAIMS

Please cancel claims 1-17 without prejudice or disclaimer of the subject matter therein.

Claim 1-17 (Canceled)

Please add new claims 18-33 as follows:

Claim 18 (New): A process for forming a thin metal oxide film, comprising the steps of:

molding an amorphous powder of organic metal chelate complexes to obtain a target, and

subjecting the target to a PVD process, thereby forming the thin metal oxide film.

Claim 19 (New): The process for forming the thin metal oxide film according to claim 18, further comprising:

mixing metallic materials with an organic chelating agent so as to give a predetermined metal composition to prepare a transparent aqueous solution of organic metal chelate complexes, and

Application No.: filed concurrently  
Preliminary Amendment  
July 8, 2003

spray-drying the aqueous solution to obtain an amorphous powder of the organic metal chelate complexes.

Claim 20 (New): The process for forming the thin metal oxide film according to claim 19, wherein the organic metal chelate complexes are mixed homogenously with each other at a molecular level in the amorphous powder.

Claim 21 (New): The process for forming the thin metal oxide film according to claim 19, wherein the organic chelating agent is an amino-carboxylic acid chelating agent which is not thermally decomposed at a temperature of 200 °C or less.

Claim 22 (New): The process for forming the thin metal oxide film according to claim 19, wherein the organic chelating agent with at least stoichiometric quantity of the metallic materials is mixed with the metallic materials to allow all of the metallic materials for forming complex salts to prepare the transparent aqueous solution.

Claim 23 (New): The process for forming the thin metal oxide film according to claim 19, further comprising adding at least one of a reducing agent and an antioxidant to the aqueous

Application No.: filed concurrently  
Preliminary Amendment  
July 8, 2003

solution of the organic chelate complexes to prevent the oxidation of metal ions therein.

Claim 24 (New): The process for forming the thin metal oxide film according to claim 19, wherein the organic metal chelate complexes are multi-element organic metal chelate complexes.

Claim 25 (New): The process for forming the thin metal oxide film according to claim 18, wherein the target is in the shape of a tablet.

Claim 26 (New): The process for forming the thin metal oxide film according to claim 19, wherein the target is in the shape of a tablet.

Claim 27 (New): The process for forming the thin metal oxide film according to claim 18, wherein said step of molding of the amorphous powder is conducted at the pressure of 200 to 1000 Kg/m<sup>3</sup>.

Claim 28 (New): The process for forming the thin metal oxide film according to claim 19, wherein said step of molding of

Application No.: filed concurrently  
Preliminary Amendment  
July 8, 2003

the amorphous powder is conducted at the pressure of 200 to 1000 Kg/m<sup>3</sup>.

Claim 29 (New): The process for forming the thin metal oxide film according to claim 18, wherein the PVD process is a laser deposition method.

Claim 30 (New): The process for forming the thin metal oxide film according to claim 29, wherein the laser deposition method includes:

irradiating a laser on the target,  
forming minute uniform clusters, and  
depositing the clusters on a heated substrate.

Claim 31 (New): The process for forming the thin metal oxide film according to claim 30, wherein the irradiating the laser is conducted in an oxygen atmosphere.

Claim 32 (New): The process for forming the thin metal oxide film according to claim 18, wherein the thin metal oxide film is a thin film of YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7-δ</sub>.

Application No.: filed concurrently  
Preliminary Amendment  
July 8, 2003

Claim 33 (New): The process for forming the thin metal oxide film according to claim 18, wherein the thin metal oxide film is a thin film of  $\text{SrTiO}_3$ .